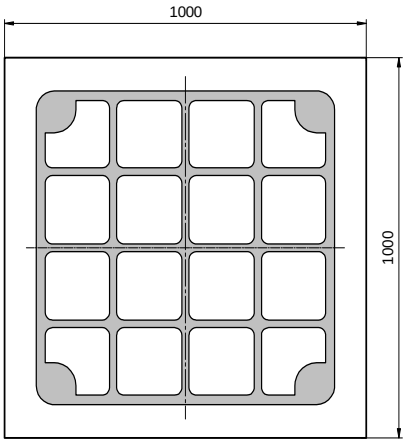
LED - Chip

ELC-850-11

26.04.2012 rev. 07

Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up



typ. dimensions (µm)

typ. thickness
180 µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm
structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.35	1.5	V
Forward voltage[2]	I_F = 350 mA	V_F		1.8		V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e		4		mW
Radiant power[2]	I_F = 350 mA	Φ_e		60		mW
Radiant power[3]	I_F = 350 mA	Φ_e		100		mW
Peak wavelength	I_F = 20 mA	λ_P	840	850	860	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		45		nm
Switching time	I_F = 20 mA	t_r, t_f		15		ns

[1]Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment
[2]Measured on bare chip glued on a Ø 8 x 1mm Cu header (10 s after switched on)
[3]Measured on epoxy covered chip glued on a Ø 8 x 1mm Cu header (10 s after switched on)

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-850-11				

Packing: Chips on adhesive film with wire-bond side on top

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